NSN 5961-01-381-8184

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View Online at https://aerobasegroup.com/nsn/5961-01-381-8184
Inclosure Material:
Metal
Overall Length:
Between 0.645 inches and 0.665 inches
Overall Height:
Between 0.190 inches and 0.200 inches
Overall Width:
Between 0.410 inches and 0.420 inches
Mounting Facility Quantity:
1
Internal Configuration:
Field effect
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-257
Mounting Method:
Terminal and unthreaded hole
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
500.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source and 20.0 gate to source voltage
Current Rating Per Characteristic:
4.50 amperes drain current and 15.00 amperes off-state current, peak
Power Rating Per Characteristic:
50.0 watts total device dissipation
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius junction
Special Test Features:
Environmental stress screening
Test Data Document:
08748-tr162 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing) and 08748-tr169 drawing (this
is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification,
standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
3 uninsulated wire lead
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
Yes - demil/mli

Fiig: A110a0